# SN65C3238, SN75C3238 3-V TO 5.5-V MULTICHANNEL RS-232 COMPATIBLE LINE DRIVER/RECEIVER

SLLS352F - JUNE 1999 - REVISED OCTOBER 2004

Auto-powerdown Plus     Overest With S. V. La F. F. V. V. Complete	DB, DW, OR PW PACKAGE (TOP VIEW)
<ul> <li>Operate With 3-V to 5.5-V V<sub>CC</sub> Supply</li> </ul>	, ,
<ul> <li>Always-Active Noninverting Receiver</li> </ul>	C2+[] 1 28 ] C1+
Output (ROUT1B)	GND [ 2 27 ] V+
<ul> <li>Support Operation From 250 kbit/s to</li> </ul>	C2-[]3 26 ]] V <sub>CC</sub>
1 Mbit/s	V-[] 4 25 ] C1-
Low Standby Current 1 μA Typ	DOUT1 [ 5 24 ] DIN1
• External Capacitors 4 × 0.1 μF	DOUT2 [ 6 23 ] DIN2
•	DOUT3 🛛 7 22 🗓 DIN3
<ul> <li>Accept 5-V Logic Input With 3.3-V Supply</li> </ul>	RIN1 8 21 ROUT1
<ul><li>Inter-Operable With SN65C3243,</li></ul>	RIN2 🛮 9 20 🗓 ROUT2
SN75C3243	DOUT4 🛛 10 19 🗍 DIN4
<ul> <li>RS-232 Bus-Pin ESD Protection Exceeds</li> </ul>	RIN3 🛚 11 18 🕽 ROUT3
±15-kV Using Human-Body Model (HBM)	DOUT5 [ 12 17 ] DIN5
Applications	FORCEON [] 13 16 ] ROUT1B
<ul> <li>Battery-Powered Systems, PDAs,</li> </ul>	FORCEOFF [ 14 15 ] INVALID
Notebooks, Sub-Notebooks, Laptops,	
Palmtop PCs, Hand-Held Equipment,	

### description/ordering information

Modems, and Printers

The 'C3238 devices consist of five line drivers, three line receivers, and a dual charge-pump circuit with  $\pm 15$ -kV ESD protection pin to pin (serial-port connection pins, including GND). The charge pump and four small external capacitors allow operation from a single 3-V to 5.5-V supply. In addition, these devices include an always-active noninverting output (ROUT1B), which allows applications using the ring indicator to transmit data while the device is powered down. These devices operate at data signaling rates up to 1 Mbit/s and at an increased slew-rate range of 24 V/ $\mu$ s to 150 V/ $\mu$ s.

### ORDERING INFORMATION

TA	PACKAG	ΕŤ	ORDERABLE PART NUMBER	TOP-SIDE MARKING
	0010 (DM)	Tube of 20	SN75C3238DW	7500000
	SOIC (DW)	Reel of 1000	SN75C3238DWR	75C3238
−0°C to 70°C	SSOP (DB)	Reel of 2000	SN75C3238DBR	75C3238
	TOOOD (DIA)	Tube of 50	SN75C3238PW	040000
	TSSOP (PW)	Reel of 2000	SN75C3238PWR	CA3238
	0010 (DW)	Tube of 20	SN65C3238DW	0500000
	SOIC (DW)	Reel of 1000	SN65C3238DWR	65C3238
-40°C to 85°C	SSOP (DB)	Reel of 2000	SN65C3238DBR	65C3238
	TCCOD (DIAN)	Tube of 50	SN65C3238PW	CD2020
	TSSOP (PW)	Reel of 2000	SN65C3238PWR	CB3238

<sup>†</sup> Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



### description/ordering information (continued)

Flexible control options for power management are featured when the serial-port and driver inputs are inactive. The auto-powerdown plus feature functions when FORCEON is low and FORCEOFF is high. During this mode of operation, if the device does not sense valid signal transitions on all receiver and driver inputs for 30 s, the built-in charge-pump and drivers are powered down, reducing the supply current to 1 μA. By disconnecting the serial port or placing the peripheral drivers off, auto-powerdown plus will occur if there is no activity in the logic levels for the driver inputs. Auto-powerdown plus can be disabled when FORCEON and FORCEOFF are high. With auto-powerdown plus enabled, the device automatically activates once a valid signal is applied to any receiver or driver input. INVALID is high (valid data) if any receiver input voltage is greater than 2.7 V or less than –2.7 V or has been between –0.3 V and 0.3 V for less than 30 μs. INVALID is low (invalid data) if all receiver input voltages are between -0.3 V and 0.3 V for more than 30 µs. Refer to Figure 5 for receiver input levels.

### **Function Tables**

#### **EACH DRIVER**

		INPU	TS	OUTPUT	
DIN	FORCEON	FORCEOFF	TIME ELAPSED SINCE LAST RIN OR DIN TRANSITION	DOUT	DRIVER STATUS
Х	Х	L	X	Z	Powered off
L	Н	Н	Х	Н	Normal operation with
Н	Н	Н	X	L	auto-powerdown plus disabled
L	L	Н	<30 s	Н	Normal operation with
Н	L	Н	<30 s	L	auto-powerdown plus enabled
L	L	Н	>30 s	Z	Powered off by
Н	L	Н	>30 s	Z	auto-powerdown plus feature

H = high level, L = low level, X = irrelevant, Z = high impedance

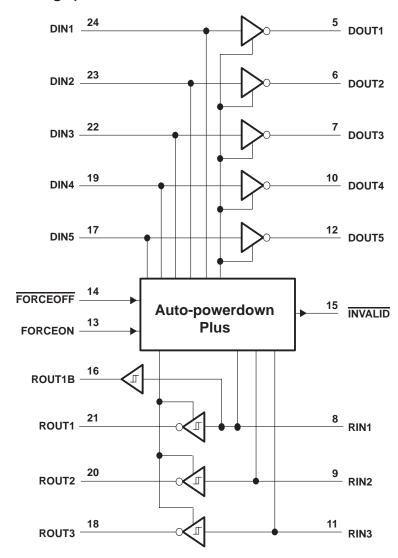
### **EACH RECEIVER**

		INPUT	S	OUTP	UTS	
RIN2	RIN1, RIN3–RIN5	FORCEOFF	TIME ELAPSED SINCE LAST RIN OR DIN TRANSITION	ROUT1B	ROUT	RECEIVER STATUS
L	Χ	L	Х	L	Z	Powered off while
Н	Χ	L	X	Н	Z	ROUT1B is active
L	L	Н	<30 s	L	Н	
L	Н	Н	<30 s	L	L	Normal operation with
Н	L	Н	<30 s	Н	Н	auto-powerdown plus
Н	Н	Н	<30 s	Н	L	disabled/enabled
Open	Open	Н	>30 s	L	Н	

H = high level, L = low level, X = irrelevant, Z = high impedance (off), Open = input disconnected or connected driver off



# logic diagram (positive logic)



# absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range, V <sub>CC</sub> (see Note 1)	0.3 V to 6 V
Positive output supply voltage range, V+ (see Note 1)	
Negative output supply voltage range, V– (see Note 1)	0.3 V to -7 V
Supply voltage difference, V+ – V– (see Note 1)	13 V
Input voltage range, V <sub>I</sub> : Driver (FORCEOFF, FORCEON)	0.3 V to 6 V
Receiver	–25 V to 25 V
Output voltage range, V <sub>O</sub> : Driver	– 13.2 V to 13.2 V
Receiver (INVALID)	$\dots$ -0.3 V to V <sub>CC</sub> + 0.3 V
Package thermal impedance, $\theta_{JA}$ (see Notes 2 and 3): DB package .	62°C/W
DW package	46°C/W
PW package	62°C/W
Operating virtual junction temperature, T <sub>J</sub>	150°C
Storage temperature range, T <sub>stq</sub>	–65°C to 150°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltages are with respect to network GND.
  - 2. Maximum power dissipation is a function of  $T_J(max)$ ,  $\theta_{JA}$ , and  $T_A$ . The maximum allowable power dissipation at any allowable ambient temperature is  $P_D = (T_J(max) T_A)/\theta_{JA}$ . Operating at the absolute maximum  $T_J$  of 150°C can affect reliability.
  - 3. The package thermal impedance is calculated in accordance with JESD 51-7.

# recommended operating conditions (see Note 4 and Figure 6)

				MIN	NOM	MAX	UNIT
	Cumhuyaltaga		V <sub>CC</sub> = 3.3 V	3	3.3	3.6	.,
	Supply voltage		$V_{CC} = 5 V$	4.5	5	5.5	V
.,	Driver and control bink level involved	DIN, FORCEOFF, FORCEON	V <sub>CC</sub> = 3.3 V	2			٧
VIH	Driver and control high-level input voltage	DIN, FORCEOFF, FORCEON	V <sub>CC</sub> = 5 V	2.4			V
V <sub>IL</sub>	Driver and control low-level input voltage	DIN, FORCEOFF, FORCEON				8.0	V
٧ <sub>I</sub>	Driver and control input voltage	DIN, FORCEOFF, FORCEON		0		5.5	V
٧ <sub>I</sub>	Receiver input voltage			-25		25	V
Τ.			SN75C3238	0		70	20
TA	Operating free-air temperature		SN65C3238	-40		85	°C

NOTE 4: Testing supply conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V  $\pm$  0.15 V; C1–C4 = 0.22  $\mu$ F at V<sub>CC</sub> = 3.3 V  $\pm$  0.3 V; and C1 = 0.047  $\mu$ F and C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V  $\pm$  0.5 V.

# electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 6)

PARAMETER		TEST CONDITIONS	MIN	TYP‡	MAX	UNIT	
lį	Input leakage current	FORCEOFF, FORCEON			±0.01	±1	μΑ
		Auto-powerdown plus disabled	No load, FORCEOFF and FORCEON at V <sub>CC</sub>		0.5	2	mA
Icc	Supply current	Powered off	No load, FORCEOFF at GND		1	10	
icc	Сарру остол	Auto-powerdown plus enabled	No load, FORCEOFF at V <sub>CC</sub> , FORCEON at GND, All RIN are open or grounded		1	10	μΑ

<sup>&</sup>lt;sup>‡</sup> All typical values are at  $V_{CC} = 3.3 \text{ V}$  or  $V_{CC} = 5 \text{ V}$ , and  $T_A = 25^{\circ}\text{C}$ .

NOTE 4: Testing supply conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V  $\pm$  0.15 V; C1–C4 = 0.22  $\mu$ F at V<sub>CC</sub> = 3.3 V  $\pm$  0.3 V; and C1 = 0.047  $\mu$ F and C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V  $\pm$  0.5 V.



### **DRIVER SECTION**

# electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 6)

	PARAMETER	TES	ST CONDITIONS	6	MIN	TYP <sup>†</sup>	MAX	UNIT
Vон	High-level output voltage	All DOUT at $R_L = 3 \text{ k}\Omega$ to	GND		5	5.4		V
VOL	Low-level output voltage	All DOUT at $R_L = 3 \text{ k}\Omega$ to	GND		-5	-5.4		V
lн	High-level input current	VI = VCC				±0.01	±1	μΑ
Ι <sub>Ι</sub> L	Low-level input current	V <sub>I</sub> at GND				±0.01	±1	μΑ
	Object along the standard access of	V <sub>CC</sub> = 3.6 V,	VO = 0 V			±35	±60	A
los	Short-circuit output current‡	V <sub>CC</sub> = 5.5 V,	VO = 0 V			±40	±90	mA
r <sub>O</sub>	Output resistance	$V_{CC}$ , V+, and V- = 0 V,	V <sub>O</sub> = ±2 V		300	10M		Ω
1	Output lookage ourrent	FORCEOFF = GND	$V_0 = \pm 12 \text{ V},$	$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$			±25	^
loff	Output leakage current	FORCEOFF = GND	$V_0 = \pm 10 \text{ V},$	V <sub>CC</sub> = 4.5 V to 5.5 V			±25	μА

<sup>&</sup>lt;sup>†</sup> All typical values are at  $V_{CC} = 3.3 \text{ V}$  or  $V_{CC} = 5 \text{ V}$ , and  $T_A = 25^{\circ}\text{C}$ .

# switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 6)

	PARAMETER	1	TEST CONDITIONS		MIN	TYP	MAX	UNIT
			C <sub>L</sub> = 1000 pF		250			
	Maximum data rate (see Figure 1)	$R_L = 3 \text{ k}\Omega$ , One DOUT switching	$C_L = 250 \text{ pF},$	V <sub>CC</sub> = 3 V to 4.5 V	1000			kbit/s
	(acc rigare r)	One Boot switching	$C_L = 1000 \text{ pF}, \qquad V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		1000			
tsk(p)	Pulse skew§	$C_L = 150 \text{ pF to } 2500 \text{ pF},$	$R_L = 3 k\Omega$ to $7 k\Omega$ ,	See Figure 2		25		ns
SR(tr)	Slew rate, transition region (see Figure 1)	C <sub>L</sub> = 150 pF to 1000 pF,	$R_L = 3 \text{ k}\Omega \text{ to } 7 \text{ k}\Omega,$	V <sub>CC</sub> = 3.3 V	18		150	V/µs

<sup>&</sup>lt;sup>†</sup> All typical values are at  $V_{CC} = 3.3 \text{ V}$  or  $V_{CC} = 5 \text{ V}$ , and  $T_A = 25^{\circ}\text{C}$ .



<sup>&</sup>lt;sup>‡</sup> Short-circuit durations should be controlled to prevent exceeding the device absolute power-dissipation ratings, and not more than one output should be shorted at a time.

NOTE 4: Testing supply conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V  $\pm$  0.15 V; C1–C4 = 0.22  $\mu$ F at V<sub>CC</sub> = 3.3 V  $\pm$  0.3 V; and C1 = 0.047  $\mu$ F and C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V  $\pm$  0.5 V.

<sup>§</sup> Pulse skew is defined as |tplH - tpHL| of each channel of the same device.

NOTE 4: Testing supply conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V  $\pm$  0.15 V; C1–C4 = 0.22  $\mu$ F at V<sub>CC</sub> = 3.3 V  $\pm$  0.3 V; and C1 = 0.047  $\mu$ F and C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V  $\pm$  0.5 V.

### RECEIVER SECTION

# electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4 and Figure 6)

	PARAMETER	TEST CONDITIONS	MIN	TYP <sup>†</sup>	MAX	UNIT
Vон	High-level output voltage	I <sub>OH</sub> = -1 mA	V <sub>CC</sub> – 0.6 V	V <sub>CC</sub> – 0.1 V		V
VOL	Low-level output voltage	I <sub>OL</sub> = 1.6 mA			0.4	V
.,	Design as the format three should reduce to	V <sub>CC</sub> = 3.3 V		1.5	2.4	
V <sub>IT+</sub>	Positive-going input threshold voltage	V <sub>CC</sub> = 5 V		1.8	2.4	٧
.,	No netter material tendent through a laboration	V <sub>CC</sub> = 3.3 V	0.6	1.2		.,
V <sub>IT</sub> _	Negative-going input threshold voltage	V <sub>CC</sub> = 5 V	0.8	1.5		V
V <sub>hys</sub>	Input hysteresis (V <sub>IT+</sub> - V <sub>IT-</sub> )			0.3		V
l <sub>off</sub>	Output leakage current (except ROUT1B)	FORCEOFF = 0 V		±0.05	±10	μΑ
rį	Input resistance	$V_1 = \pm 3 \text{ V to } \pm 25 \text{ V}$	3	5	7	kΩ

<sup>&</sup>lt;sup>†</sup> All typical values are at  $V_{CC} = 3.3 \text{ V}$  or  $V_{CC} = 5 \text{ V}$ , and  $T_A = 25^{\circ}\text{C}$ .

# switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Note 4)

	PARAMETER	TEST CONDITIONS	MIN	TYP†	MAX	UNIT
tPLH	Propagation delay time, low- to high-level output	0 450 5 0 5		150		ns
tPHL	Propagation delay time, high- to low-level output	C <sub>L</sub> = 150 pF, See Figure 3		150		ns
ten	Output enable time	0 450 5 5 0 0 0 5		200		ns
tdis	Output disable time	$C_L = 150 \text{ pF}, R_L = 3 \text{ k}\Omega, \text{See Figure 4}$		200		ns
tsk(p)	Pulse skew <sup>‡</sup>	See Figure 3		50		ns

 $<sup>\</sup>overline{\dagger}$  All typical values are at V<sub>CC</sub> = 3.3 V or V<sub>CC</sub> = 5 V, and T<sub>A</sub> = 25°C.



NOTE 4: Testing supply conditions are C1–C4 =  $0.1~\mu\text{F}$  at  $V_{CC}$  =  $3.3~V \pm 0.15~V$ ; C1–C4 =  $0.22~\mu\text{F}$  at  $V_{CC}$  =  $3.3~V \pm 0.3~V$ ; and C1 =  $0.047~\mu\text{F}$  and C2–C4 =  $0.33~\mu\text{F}$  at  $V_{CC}$  =  $5~V \pm 0.5~V$ .

<sup>‡</sup> Pulse skew is defined as |tpLH - tpHL| of each channel of the same device.

NOTE 4: Testing supply conditions are C1–C4 = 0.1  $\mu$ F at V<sub>CC</sub> = 3.3 V  $\pm$  0.15 V; C1–C4 = 0.22  $\mu$ F at V<sub>CC</sub> = 3.3 V  $\pm$  0.3 V; and C1 = 0.047  $\mu$ F and C2–C4 = 0.33  $\mu$ F at V<sub>CC</sub> = 5 V  $\pm$  0.5 V.

### **AUTO-POWERDOWN PLUS SECTION**

# electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

	PARAMETER	TEST CONDITIONS	MIN	TYP <sup>†</sup>	MAX	UNIT
V <sub>T+(valid)</sub>	Receiver input threshold for INVALID high-level output voltage	FORCEON = GND, FORCEOFF = V <sub>CC</sub>			2.7	V
VT–(valid)	Receiver input threshold for INVALID high-level output voltage	FORCEON = GND, FORCEOFF = V <sub>CC</sub>	-2.7			V
VT(invalid)	Receiver input threshold for INVALID low-level output voltage	FORCEON = GND, FORCEOFF = V <sub>CC</sub>	-0.3		0.3	V
VOH	INVALID high-level output voltage	I <sub>OH</sub> = -1 mA, FORCEON = GND, FORCEOFF = V <sub>CC</sub>	V <sub>CC</sub> - 0.6			V
VOL	INVALID low-level output voltage	I <sub>OL</sub> = 1.6 mA, FORCEON = GND, FORCEOFF = V <sub>CC</sub>			0.4	V

 $<sup>\</sup>overline{\dagger}$  All typical values are at V<sub>CC</sub> = 3.3 V or V<sub>CC</sub> = 5 V, and T<sub>A</sub> = 25°C.

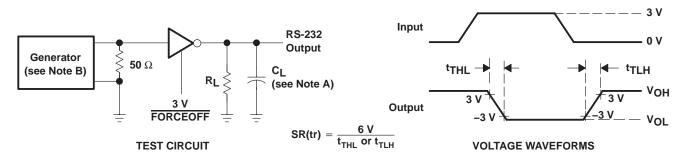
# switching characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted) (see Figure 5)

	PARAMETER	MIN	TYP†	MAX	UNIT
tvalid	Propagation delay time, low- to high-level output		0.1		μs
tinvalid	Propagation delay time, high- to low-level output		50		μs
t <sub>en</sub>	Supply enable time		25		μs
t <sub>dis</sub>	Receiver or driver edge to auto-powerdown plus	15	30	60	s

<sup>&</sup>lt;sup>†</sup> All typical values are at  $V_{CC} = 3.3 \text{ V}$  or  $V_{CC} = 5 \text{ V}$ , and  $T_A = 25^{\circ}\text{C}$ .



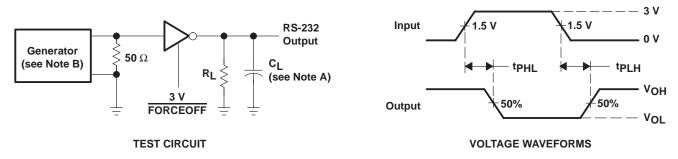
### PARAMETER MEASUREMENT INFORMATION



NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 1 Mbit/s,  $Z_{\Omega}$  = 50  $\Omega$ , 50% duty cycle,  $t_r \le 10$  ns,  $t_f \le 10$  ns.

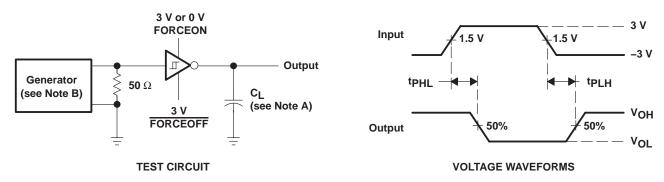
Figure 1. Driver Slew Rate



NOTES: A. C<sub>I</sub> includes probe and jig capacitance.

B. The pulse generator has the following characteristics: PRR = 1 Mbit/s,  $Z_O = 50 \Omega$ , 50% duty cycle,  $t_f \le 10$  ns,  $t_f \le 10$  ns.

Figure 2. Driver Pulse Skew



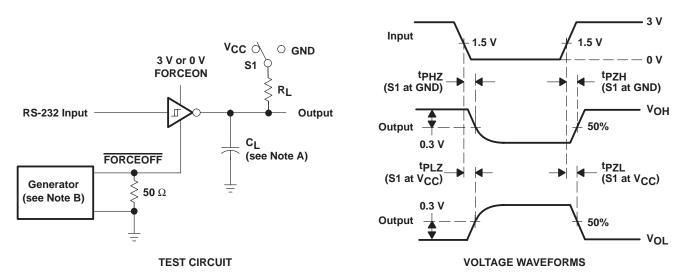
NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

B. The pulse generator has the following characteristics:  $Z_O = 50 \Omega$ , 50% duty cycle,  $t_f \le 10 \text{ ns}$ ,  $t_f \le 10 \text{ ns}$ .

Figure 3. Receiver Propagation Delay Times



### PARAMETER MEASUREMENT INFORMATION

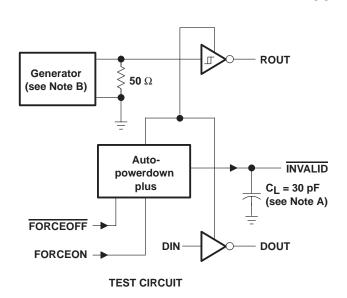


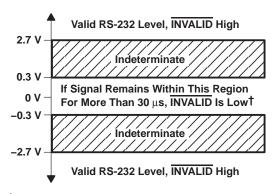
NOTES: A. C<sub>L</sub> includes probe and jig capacitance.

- B. The pulse generator has the following characteristics:  $Z_O = 50 \Omega$ , 50% duty cycle,  $t_f \le 10$  ns.  $t_f \le 10$  ns.
- C. tpLz and tpHz are the same as tdis.
- D. tpZL and tpZH are the same as ten.

Figure 4. Receiver Enable and Disable Times

### PARAMETER MEASUREMENT INFORMATION





 $\mbox{\dagger}$  Auto-powerdown plus disables drivers and reduces supply current to 1  $\mu A.$ 

- NOTES: A. C<sub>L</sub> includes probe and jig capacitance.
  - B. The pulse generator has the following characteristics: PRR = 5 kbit/s,  $Z_O$  = 50  $\Omega$ , 50% duty cycle,  $t_f \le 10$  ns,  $t_f \le 10$  ns.

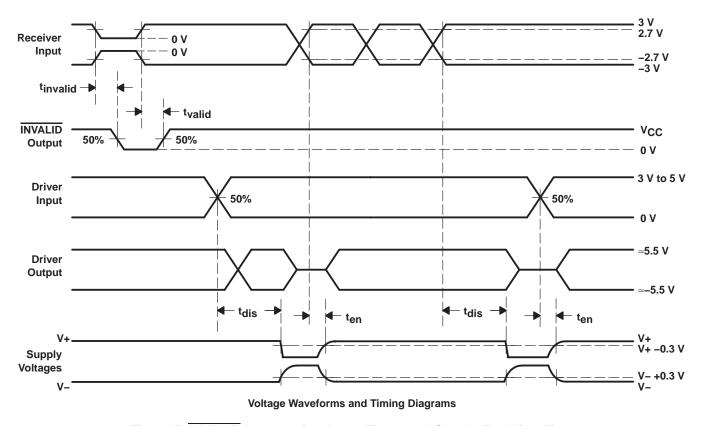
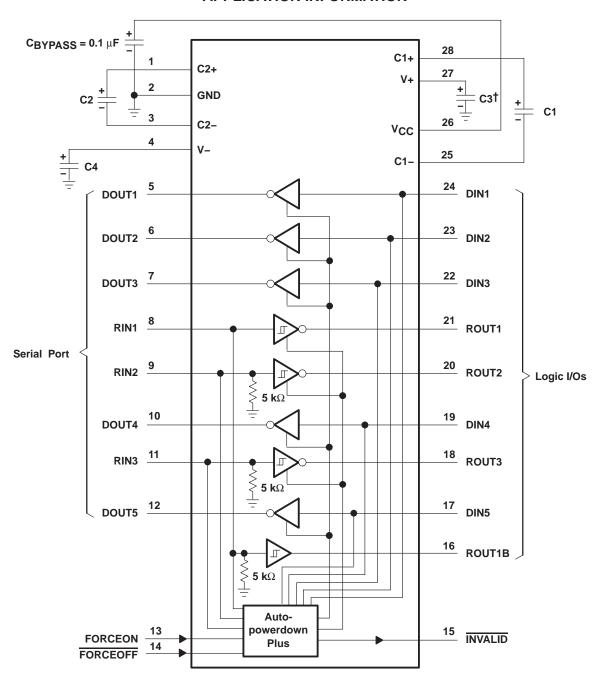


Figure 5. INVALID Propagation Delay Times and Supply Enabling Time



### **APPLICATION INFORMATION**



 $^\dagger\text{C3}$  can be connected to VCC or GND.

NOTE A: Resistor values shown are nominal.

V<sub>CC</sub> vs CAPACITOR VALUES

VCC	C1	C2, C3, and C4
$  \begin{array}{c} \textbf{3.3 V} \pm \textbf{0.15 V} \\ \textbf{3.3 V} \pm \textbf{0.3 V} \\ \textbf{5 V} \pm \textbf{0.5 V} \\ \textbf{3 V to 5.5 V} \\ \end{array} $	0.1 μF 0.22 μF 0.047 μ F 0.22 μF	0.1 μF 0.22 μF 0.33 μF 1 μF

Figure 6. Typical Operating Circuit and Capacitor Values







i.com 4-Mar-2005

### **PACKAGING INFORMATION**

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp <sup>(3)</sup>
SN65C3238DB	PREVIEW	SSOP	DB	28	50	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1 YEAR/ Level-1-235C-UNLIM
SN65C3238DBR	ACTIVE	SSOP	DB	28	2000	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1 YEAR/ Level-1-235C-UNLIM
SN65C3238DW	ACTIVE	SOIC	DW	28	20	Pb-Free (RoHS)	CU NIPDAU	Level-2-250C-1 YEAR/ Level-1-235C-UNLIM
SN65C3238DWR	ACTIVE	SOIC	DW	28	1000	Pb-Free (RoHS)	CU NIPDAU	Level-2-250C-1 YEAR/ Level-1-235C-UNLIM
SN65C3238PW	ACTIVE	TSSOP	PW	28	50	Pb-Free (RoHS)	CU NIPDAU	Level-1-250C-UNLIM
SN65C3238PWR	ACTIVE	TSSOP	PW	28	2000	Pb-Free (RoHS)	CU NIPDAU	Level-1-250C-UNLIM
SN75C3238DB	PREVIEW	SSOP	DB	28	50	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1 YEAR/ Level-1-235C-UNLIM
SN75C3238DBR	ACTIVE	SSOP	DB	28	2000	Pb-Free (RoHS)	CU NIPDAU	Level-2-260C-1 YEAR/ Level-1-235C-UNLIM
SN75C3238DW	ACTIVE	SOIC	DW	28	20	Pb-Free (RoHS)	CU NIPDAU	Level-2-250C-1 YEAR/ Level-1-235C-UNLIM
SN75C3238DWR	ACTIVE	SOIC	DW	28	1000	Pb-Free (RoHS)	CU NIPDAU	Level-2-250C-1 YEAR/ Level-1-235C-UNLIM
SN75C3238PW	ACTIVE	TSSOP	PW	28	50	Pb-Free (RoHS)	CU NIPDAU	Level-1-250C-UNLIM
SN75C3238PWR	ACTIVE	TSSOP	PW	28	2000	Pb-Free (RoHS)	CU NIPDAU	Level-1-250C-UNLIM

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND**: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - May not be currently available - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

None: Not yet available Lead (Pb-Free).

**Pb-Free** (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Green (RoHS & no Sb/Br): TI defines "Green" to mean "Pb-Free" and in addition, uses package materials that do not contain halogens, including bromine (Br) or antimony (Sb) above 0.1% of total product weight.

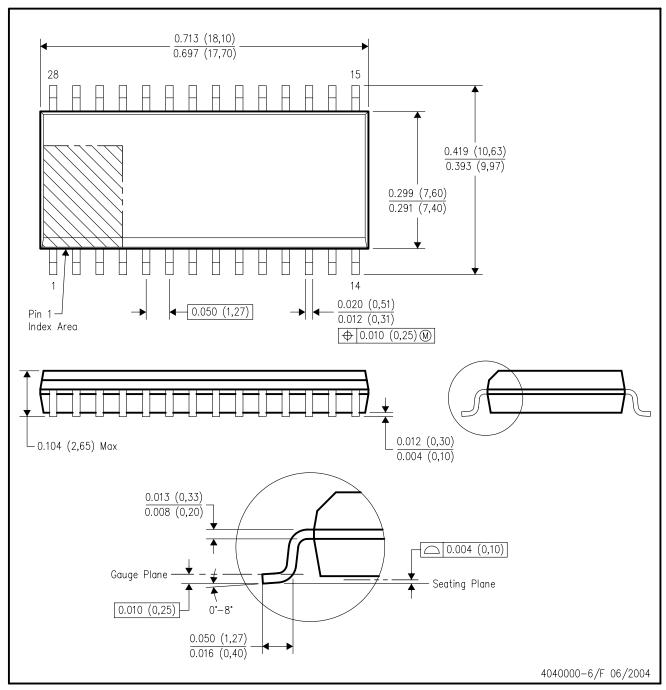
(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDECindustry standard classifications, and peak solder temperature.

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# DW (R-PDSO-G28)

# PLASTIC SMALL-OUTLINE PACKAGE



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-013 variation AE.



## DB (R-PDSO-G\*\*)

## PLASTIC SMALL-OUTLINE

### **28 PINS SHOWN**



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.

D. Falls within JEDEC MO-150

## PW (R-PDSO-G\*\*)

### 14 PINS SHOWN

## PLASTIC SMALL-OUTLINE PACKAGE



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.

D. Falls within JEDEC MO-153

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